

NCE Automotive P-Channel Super Trench Power MOSFET

Description

The NCEAP01P35AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

• V_{DS} =-100V,I_D =-35A

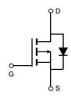
 $R_{DS(ON)}$ =35m Ω (typical) @ V_{GS} =-10V

 $R_{DS(ON)}$ =40m Ω (typical) @ V_{GS} =-4.5V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- •175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested
- AEC-Q101 qualified

Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram



Marking and pin assignment



TO-252-2Ltop view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP01P35AK	NCEAP01P35AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	-35	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-24.5	Α
Pulsed Drain Current	I _{DM}	-140	Α
Maximum Power Dissipation	P _D	105	W
Derating factor		0.7	W/°C
Single pulse avalanche energy (Note 1)	E _{AS}	320	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	ReJC	1.43	°C/W
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics			<u>'</u>			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=-250\mu A$	-1.0	-1.7	-2.2	V
David Course On Otata Basistana		V _{GS} =-10V, I _D =-20A	-	35	45	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	40	50	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-20A	-	20	-	S
Dynamic Characteristics			•	,		
Input Capacitance	Clss	50///	-	3445	-	pF
Output Capacitance	Coss	V_{DS} =-50V, V_{GS} =0V, F=1.0MHz	-	260	-	pF
Reverse Transfer Capacitance	Crss		-	6	-	pF
Switching Characteristics (Note 2)	,		'			1
Turn-on Delay Time	t _{d(on)}		-	12.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =-50 V , I_{D} =-20 A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =1.6 Ω	-	45	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	V 50V/1 00A	-	34.5	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-50V,I _D =-20A, V _{GS} =-10V	-	8.5	-	nC
Gate-Drain Charge	Q _{gd}		-	4.0	-	nC
Drain-Source Diode Characteristics	-		'			
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =-20A	-		-1.2	V
Diode Forward Current	Is		-	-	-35	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A	-	50	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	90	-	nC

Notes:

- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=-50V,VG=-10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=150°C. The SOA curve provides a single pulse rating.



Typical Electrical and Thermal Characteristics

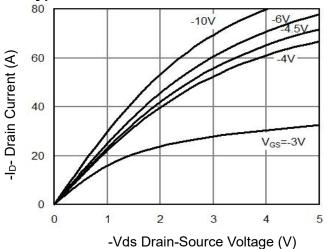


Figure 1 Output Characteristics

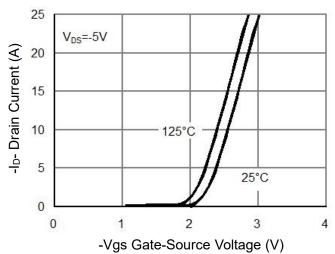


Figure 2 Transfer Characteristics

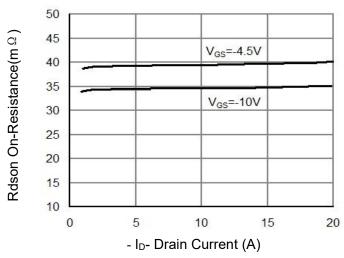


Figure 3 Rdson- Drain Current

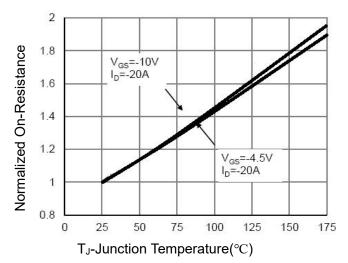


Figure 4 Rdson-JunctionTemperature

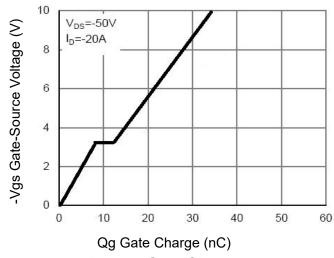


Figure 5 Gate Charge

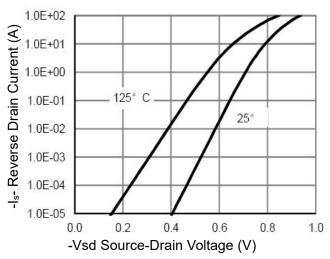


Figure 6 Source- Drain Diode Forward



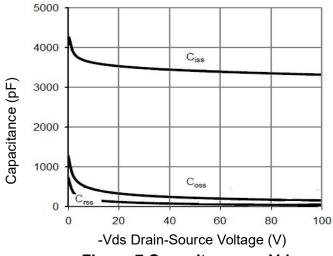


Figure 7 Capacitance vs Vds

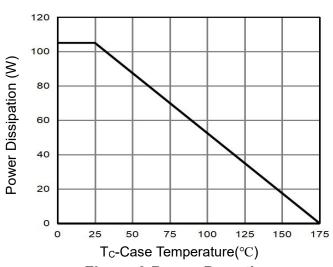


Figure 9 Power De-rating

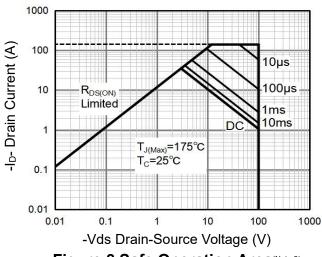


Figure 8 Safe Operation Area(Note 3)

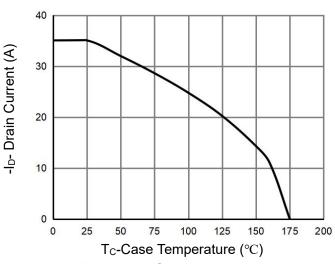


Figure 10 Current De-rating

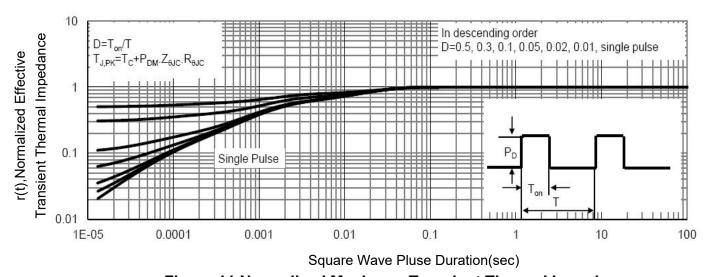
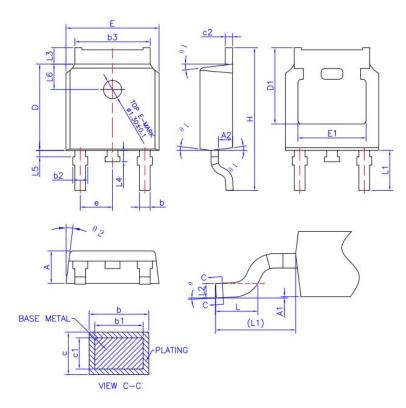


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN NOM		MAX	
Α	2.20	2.30	2.38	
A1	0	·	0.10	
A2	0.90	1.01	1.10	
b	0.72		0.85	
b1	0.71	0.76	0.81	
b2	0.72		0.90	
b3	5.13	5.33	5.46	
С	0.47		0.60	
c1	0.46	0.51	0.56	
c2	0.47		0.60	
D	6.00	6.10	6.20	
D1	5.25			
E	6.50	6.60	6.70	
E1	4.70		4/18/2007	
е	2.186 2.286		2.386	
H	9.80	10.10	10.40	
L	1.40	1.50	1.70	
L1		2.90 REF		
L2	0	.508 BSC		
L3	0.90		1.25	
L4	0.60	0.80	1.00	
L5	0.15	-	0.75	
L6	1.80 REF			
θ	0°		8°	
01	5°	7°	9°	
θ2	5°	7°	9°	



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